

Data Sheet N0668, Rev. A

16CTQ200 16CTQ200S 16CTQ200-1

RoHS 🗭

16CTQ200/16CTQ200S /16CTQ200-1 SCHOTTKY RECTIFIER

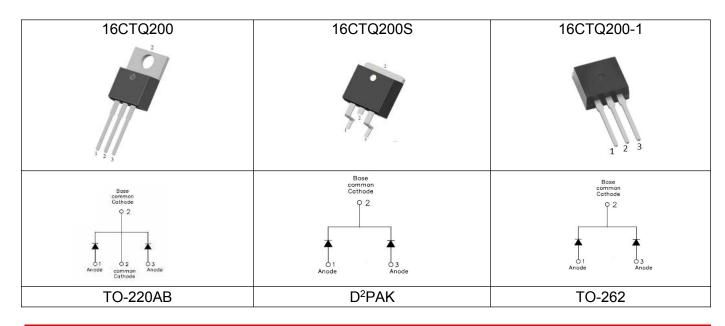
Features

Technical Data

- 175°C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=154°C, rectangular wave form	8(Per Leg) 16(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse, T _c = 25 °C	330	А

China - Germany - Korea - Singapore - United States
http://www.smc_diodes.com - sales@ smc_diodes.com

http://www.smc-diodes.com - sales@ smc-diodes.com -



16CTQ200 16CTQ200S 16CTQ200-1

RoHS 🗭

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 8A, Pulse, T _J = 25 °C	0.82	0.84	V
(Per Leg)*	V _{F2}	@ 8A, Pulse, T _J = 125 °C	0.68	0.70	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.0002	1.0	mA
	I _{R2}	$@V_R = rated V_R$ T _J = 125 °C	0.2	7.0	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	260	300	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 $\mu s, \ duty \ cycle < 2\%$

Thermal-Mechanical Specifications:

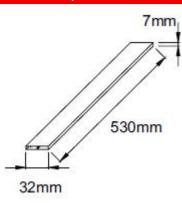
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	3.25	°C/W
Typical Thermal Resistance, Case to Heat Sink	R _{0JL}	DC operation	0.50	°C/W
Case Style	TO-220AB D ² PAK TO-262			

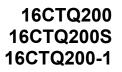
Tube Specification

Device	Package	Weight	Shipping
16CTQ200	TO-220AB	1.8g	50pcs / tube
16CTQ200S	D ² PAK	1.85g	800pcs / reel
16CTQ200-1	TO-262	1.85g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

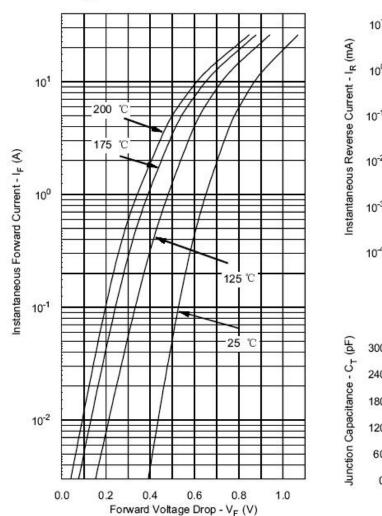
Tube Specification(TO-220AB/TO-262)





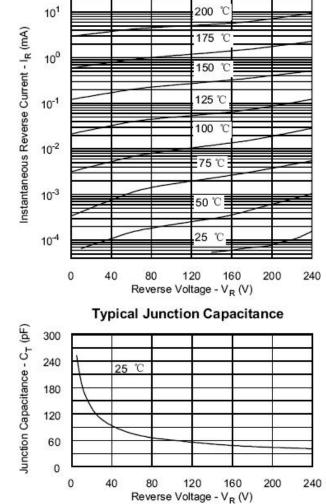
DID

Ratings and Characteristics Curves



Typical Forward Characteristics

Typical Reverse Characteristics

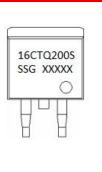


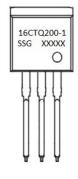




Marking Diagram







Where XXXXX is YYWWL

- = Forward Current (16A)
- = Configuration
- = Device Type
- = Reverse Voltage (200V)
- = Package type
- = SSG = Year

16

С

TQ

200

S/-1

SSG

YΥ

WW

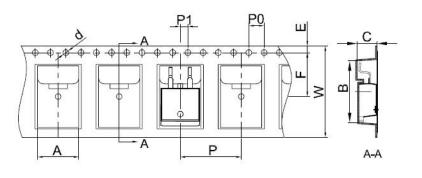
L

= Week = Lot Number

Cautions: Molding resin

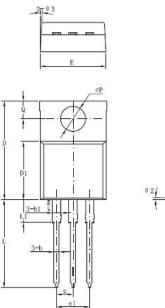
Epoxy resin UL:94V-0

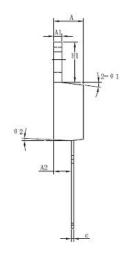
Carrier Tape Specification D²PAK



Symbol	Millimeters		
	Min.	Max.	
A	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

Mechanical Dimensions TO-220AB





Symbol	Millimeters			
	Min.	Typical	Max.	
Α	4.42	4.57	4.72	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.94	15.24	15.54	
D1	8.85	9.00	9.15	
E	10.01	10.16	10.31	
е		2.54		
e1	4.98	5.06	5.18	
H1	6.04	6.24	6.44	
L	12.7	13.56	13.80	
L1	3.56	3.5	3.96	
ΦΡ	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		7°		
Θ2		3°		
Θ3		4°		

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •

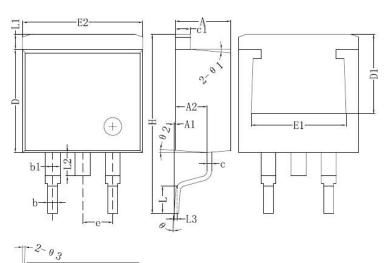
Pó RoHS

16CTQ200-1

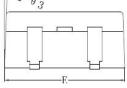
16CTQ200 16CTQ200S



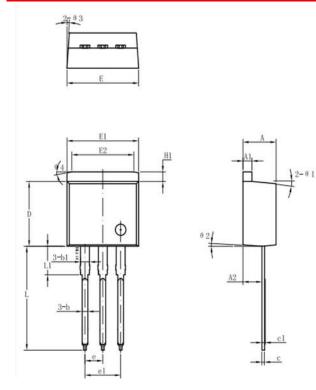
Mechanical Dimensions D²PAK



Symbol	Millimeters			
-	Min.	Typical	Max.	
Α	4.47	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.50	8.70	8.90	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.31	
е		2.54		
н	14.6	15.1	15.6	
L	2.00	2.30	2.74	
L1	1.12	1.27	1.42	
L2	1.30		2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4 °		
e3		4°		



Mechanical Dimensions TO-262



Cumb al	Millimeters			
Symbol	Min.	Typical	Max.	
Α	4.55	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1		1.27		
С	0.36	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.55	8.70	8.85	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.18	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.70	
L1	1.17	1.27	1.40	
L2			2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4 °		
e3		4°		

China - Germany - Korea - Singapore - United States http://www.smc-diodes.com - sales@ smc-diodes.com -

16CTQ200 16CTQ200S 16CTQ200-1





16CTQ200 16CTQ200S 16CTQ200-1



DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC - Sangdest Microelectronics (Nanjing) Co., Ltd sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC - Sangdest Microelectronics (Nanjing) Co., Ltd assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

4- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC - Sangdest Microelectronics (Nanjing) Co., Ltd.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC -Sangdest Microelectronics (Nanjing) Co., Ltd.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations...